

**TENTATIVE**

TOSHIBA Photocoupler GaAs Ired+Photo-Triac

## TLP763J

Office Machine

Household Use Equipment

Triac Driver

Solid State Relay

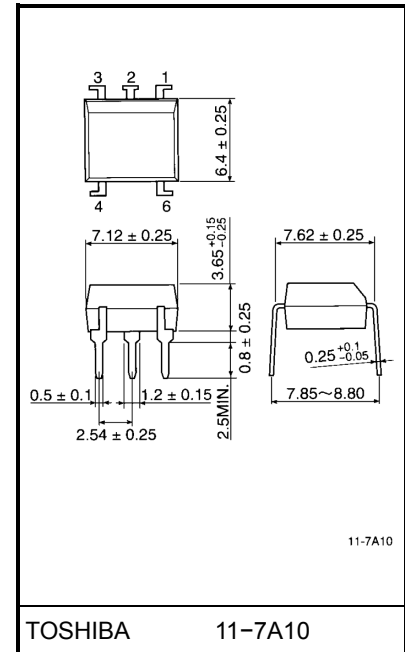
The TOSHIBA TLP763J consists of a GaAs infrared LED optically coupled to a zero voltage crossing turn-on photo-triac in a 6 lead plastic DIP.

- Peak off-state voltage: 600 V (min.)
- Trigger LED current: 10 mA (max.)
- On-state current: 100 mA (max.)
- Isolation voltage: 4000Vrms (min.)
- UL recognized: UL1577, file No. E67349
- BSI approved: BS EN60065: 1994,  
Certificate No. 7831  
BS EN60065: 1992,  
Certificate No. 7832
- SEMKO approved: SS-EN60065 (EN60065, 1993)  
SS-EN60950 (EN60950, 1992)  
SS-EN60335 (EN60335, 1988)  
Certificate No. 9522145
- Option (D4) type  
VDE approved: DIN VDE0884, 06.92  
Certificate No. 91803  
Maximum operating insulation voltage: 890 VPK  
Highest permissible over voltage: 6000 VPK

**(Note) When a VDE0884 approved type is needed,  
please designate the "option (D4)"**

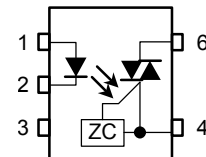
|                        | 7.62mm pich<br>TLP763J type | 10.16mm pich<br>TLP763JF type |
|------------------------|-----------------------------|-------------------------------|
| • Creepage distance    | : 7.0mm (min.)              | 8.0mm (min.)                  |
| Clearance              | : 7.0mm (min.)              | 8.0mm (min.)                  |
| Internal creepage path | : 4.0mm (min.)              | 4.0mm (min.)                  |
| Insulation thickness   | : 0.5mm (min.)              | 0.5mm (min.)                  |

Unit in mm



Weight: 0.42g

### Pin Configuration (top view)



- 1 : Anode
- 2 : Cathode
- 3 : ZC
- 4 : Triac 1
- 6 : Triac 2

## Maximum Ratings (Ta = 25°C)

| Characteristic                            |                                                         |           | Symbol              | Rating  | Unit  |
|-------------------------------------------|---------------------------------------------------------|-----------|---------------------|---------|-------|
| LED                                       | Forward current                                         |           | I <sub>F</sub>      | 50      | mA    |
|                                           | Forward current derating (Ta ≥ 53°C)                    |           | ΔI <sub>F</sub> /°C | −0.7    | mA/°C |
|                                           | Peak forward current (100 μs pulse, 100 pps)            |           | I <sub>FP</sub>     | 1       | A     |
|                                           | Reverse voltage                                         |           | V <sub>R</sub>      | 5       | V     |
|                                           | Junction temperature                                    |           | T <sub>j</sub>      | 125     | °C    |
| Detector                                  | Off-state output terminal voltage                       |           | V <sub>DRM</sub>    | 600     | V     |
|                                           | On-state RMS current                                    | Ta = 25°C | I <sub>T(RMS)</sub> | 100     | mA    |
|                                           |                                                         | Ta = 70°C |                     | 50      |       |
|                                           | On-state current derating (Ta ≥ 25°C)                   |           | ΔI <sub>T</sub> /°C | −1.1    | mA/°C |
|                                           | Peak on-state current (100μs pulse, 120pps)             |           | I <sub>TP</sub>     | 2       | A     |
|                                           | Peak nonrepetitive surge current (PW = 10 ms, DC = 10%) |           | I <sub>TSM</sub>    | 1.2     | A     |
|                                           | Junction temperature                                    |           | T <sub>j</sub>      | 115     | °C    |
| Storage temperature range                 |                                                         |           | T <sub>stg</sub>    | −55~125 | °C    |
| Operating temperature range               |                                                         |           | T <sub>opr</sub>    | −40~100 | °C    |
| Lead soldering temperature (10s)          |                                                         |           | T <sub>sol</sub>    | 260     | °C    |
| Isolation voltage (AC, 1 min., R.H.≤ 60%) |                                                         |           | BV <sub>S</sub>     | 4000    | Vrms  |

## Recommended Operating Conditions

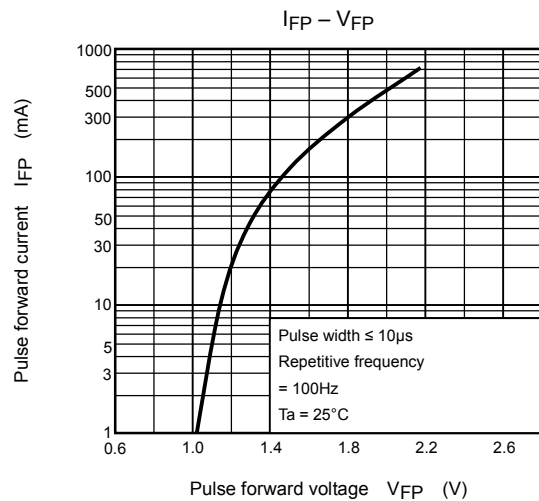
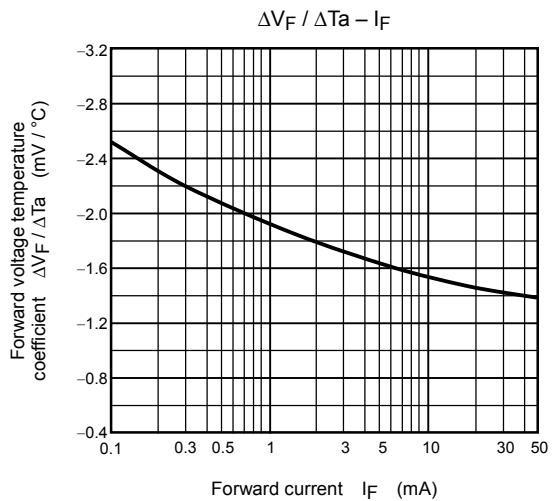
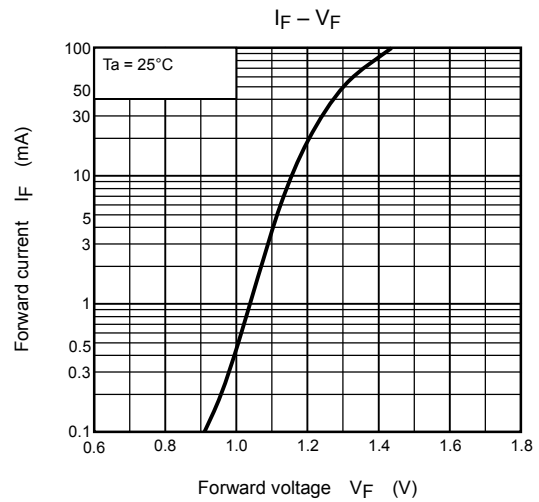
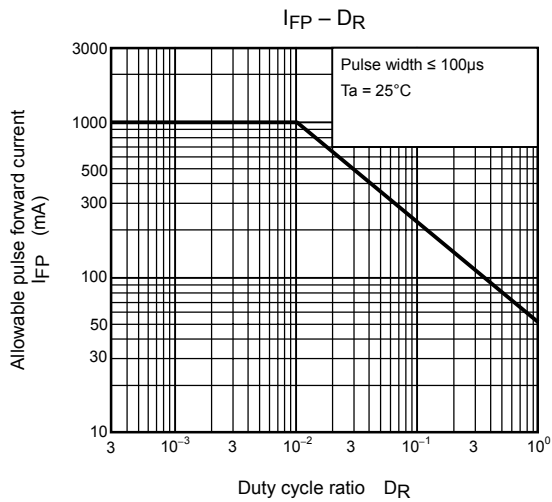
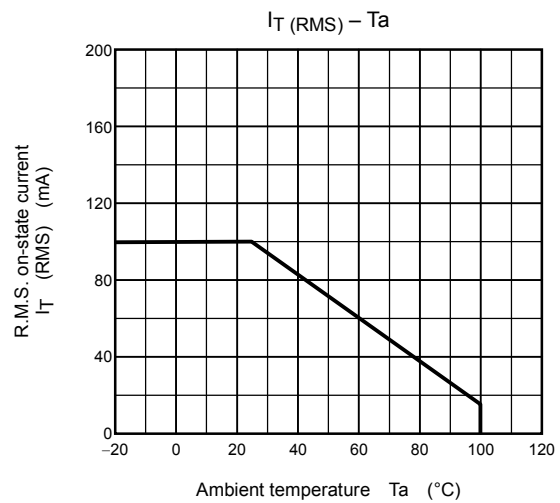
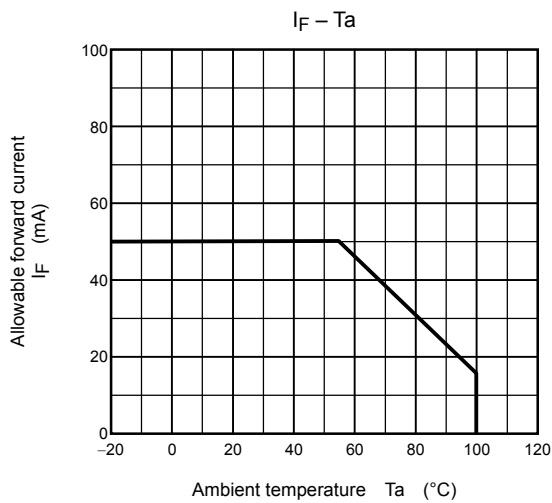
| Characteristic        | Symbol    | Min. | Typ. | Max. | Unit            |
|-----------------------|-----------|------|------|------|-----------------|
| Supply voltage        | $V_{AC}$  | —    | —    | 240  | V <sub>ac</sub> |
| Forward current       | $I_F$     | 15   | 20   | 25   | mA              |
| Peak on-state current | $I_{TP}$  | —    | —    | 1    | A               |
| Operating temperature | $T_{opr}$ | -25  | —    | 85   | °C              |

**Individual Electrical Characteristics (Ta = 25°C)**

| Characteristic |                                              | Symbol           | Test Condition                                                     | Min. | Typ. | Max. | Unit             |
|----------------|----------------------------------------------|------------------|--------------------------------------------------------------------|------|------|------|------------------|
| LED            | Forward voltage                              | $V_F$            | $I_F = 10 \text{ mA}$                                              | 1.0  | 1.15 | 1.3  | V                |
|                | Reverse current                              | $I_R$            | $V_R = 5 \text{ V}$                                                | —    | —    | 10   | $\mu\text{A}$    |
|                | Capacitance                                  | $C_T$            | $V = 0, f = 1 \text{ MHz}$                                         | —    | 30   | —    | pF               |
| Detector       | Peak off-state current                       | $I_{\text{DRM}}$ | $V_{\text{DRM}} = 600 \text{ V}$                                   | —    | 10   | 1000 | nA               |
|                | Peak on-state voltage                        | $V_{\text{TM}}$  | $I_{\text{TM}} = 100 \text{ mA}$                                   | —    | 1.7  | 3.0  | V                |
|                | Holding current                              | $I_H$            | —                                                                  | —    | 0.6  | —    | mA               |
|                | Critical rate of rise of off-state voltage   | $dv / dt$        | $V_{\text{in}} = 240 \text{ V}, T_a = 85^\circ\text{C}$            | —    | 500  | —    | V/ $\mu\text{s}$ |
|                | Critical rate of rise of commutating voltage | $dv / dt (c)$    | $I_T = 15 \text{ mA}$<br>$V_{\text{in}} = 60\text{V}_{\text{rms}}$ | —    | 0.2  | —    | V/ $\mu\text{s}$ |

**Coupled Electrical Characteristics (Ta = 25°C)**

| Characteristic                | Symbol          | Test Condition                                                              | Min.               | Typ.      | Max. | Unit             |
|-------------------------------|-----------------|-----------------------------------------------------------------------------|--------------------|-----------|------|------------------|
| Trigger LED current           | $I_{\text{FT}}$ | $V_T = 6 \text{ V}$                                                         | —                  | —         | 10   | mA               |
| Inhibit voltage               | $V_{\text{IH}}$ | $I_F = \text{rated } I_{\text{FT}}$                                         | —                  | —         | 50   | V                |
| Leakage in inhibited state    | $I_{\text{IH}}$ | $I_F = \text{rated } I_{\text{FT}}$<br>$V_T = \text{rated } V_{\text{DRM}}$ | —                  | 200       | 600  | $\mu\text{A}$    |
| Capacitance (input to output) | $C_S$           | $V_S = 0, f = 1 \text{ MHz}$                                                | —                  | 0.8       | —    | pF               |
| Isolation resistance          | $R_S$           | $V_S = 500 \text{ V}$                                                       | $1 \times 10^{12}$ | $10^{14}$ | —    | $\Omega$         |
| Isolation voltage             | $BV_S$          | AC, 1 minute                                                                | 4000               | —         | —    | $V_{\text{rms}}$ |
|                               |                 | AC, 1 second, in oil                                                        | —                  | 10000     | —    |                  |
|                               |                 | DC, 1 minute, in oil                                                        | —                  | 10000     | —    | $V_{\text{dc}}$  |



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